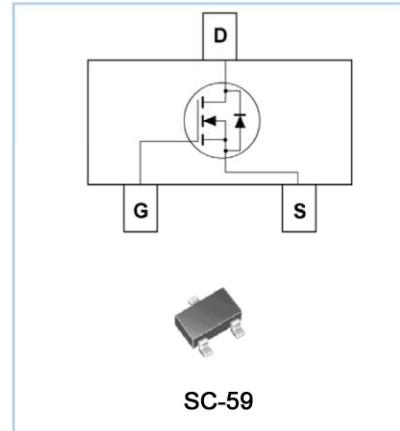


**Feature**

- 16V/6A, R<sub>DS(ON)</sub> = 50m Ω (MAX) @V<sub>GS</sub> = 4.5V.  
R<sub>DS(ON)</sub> = 55m Ω (MAX) @V<sub>GS</sub> = 2.5V.
- Super High dense cell design for extremely low R<sub>DS(ON)</sub>.
- Reliable and Rugged .
- SC-59 for Surface Mount Package .


**Applications**

- LI-ION Protection Circuit

**Absolute Maximum Ratings**

T<sub>A</sub>=25°C Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V <sub>DS</sub>	16	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Drain Current-Continuous	I <sub>D</sub>	6	A

**Electrical Characteristics**

T<sub>A</sub>=25°C Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
<b>Off Characteristics</b>						
Drain to Source Breakdown Voltage	BVDSS	V <sub>GS</sub> =0V, ID=250 μA	16	-	-	V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =6V, V <sub>GS</sub> =0V	-	-	1	μA
Gate Body Leakage Current, Forward	IGSSF	V <sub>GS</sub> =12V, V <sub>DS</sub> =0V	-	-	300	nA
Gate Body Leakage Current, Reverse	IGSSR	V <sub>GS</sub> =-12V, V <sub>DS</sub> =0V	-	-	-300	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , ID=250μA	0.4	-	1.3	V
Static Drain-source	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, ID =6.0A	-	40	50	m Ω
On-Resistance		V <sub>GS</sub> =2.5V, ID =5.2A	-	44	55	m Ω
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, IS=1.5A			1.2	V

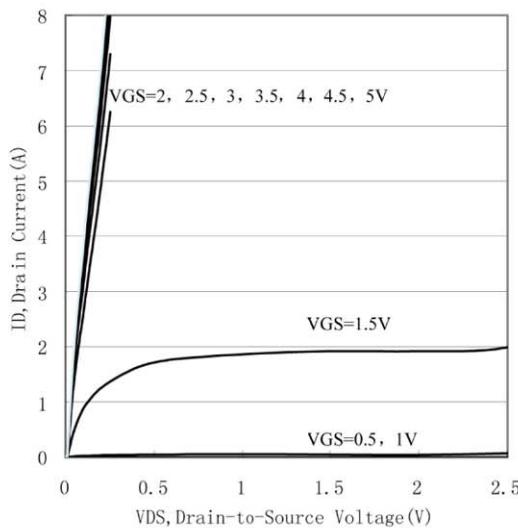
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CONSCIOUS PRODUCTS BEGIN WITH CONSCIOUS PEOPLE

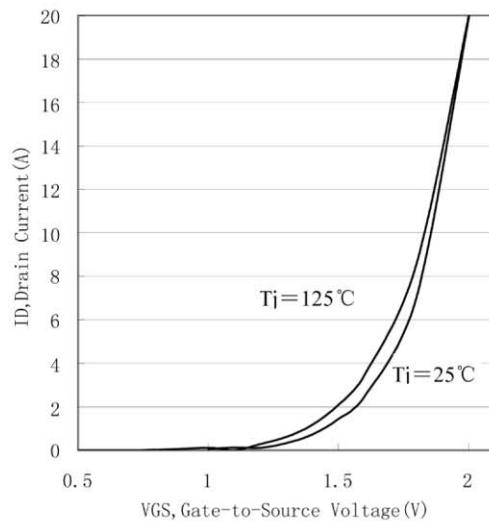
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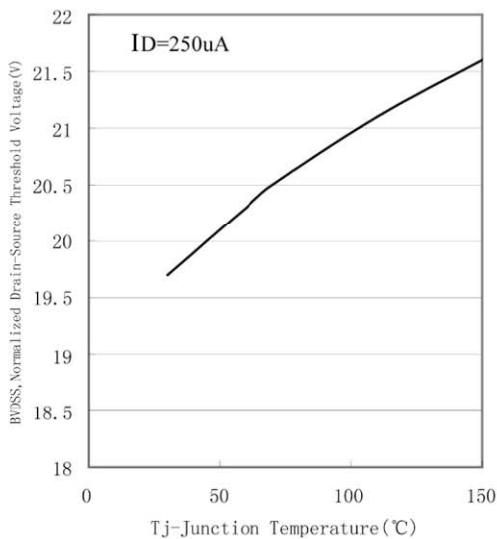
## N-Channel Enhancement Mode MOSFET Typical Characteristics



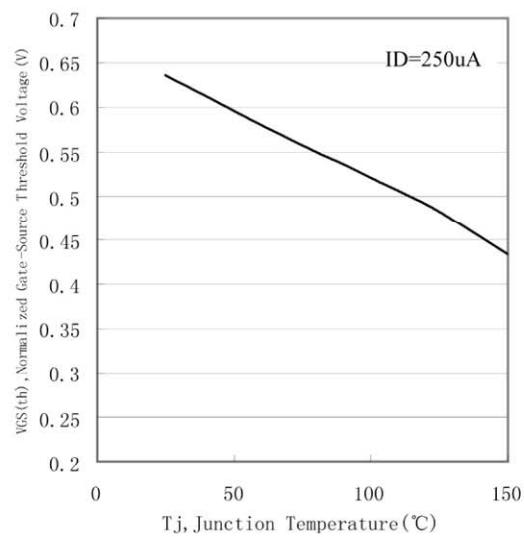
**Figure 1. Output Characteristics**



**Figure 2. Transfer Characteristics**



**Figure 3. Breakdown Voltage Variation with Temperature**



**Figure 4. Gate Threshold Variation with Temperature**

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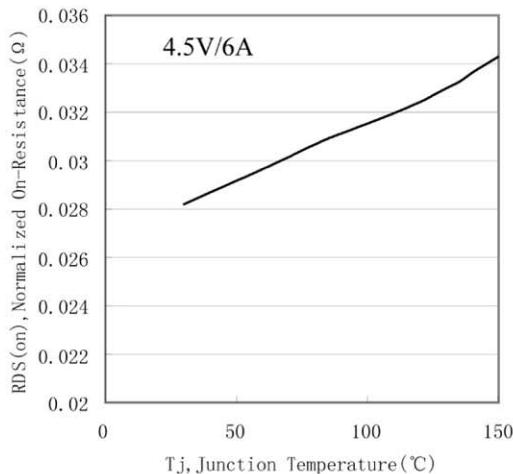
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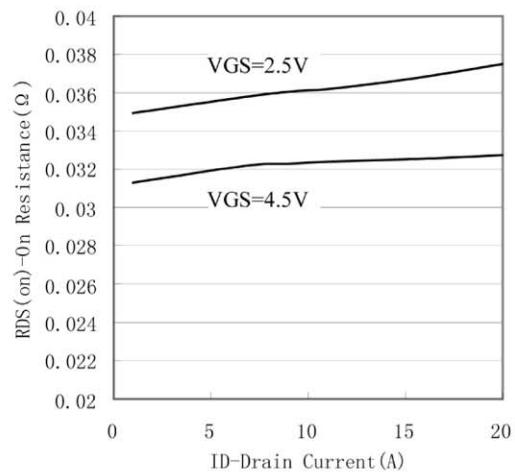


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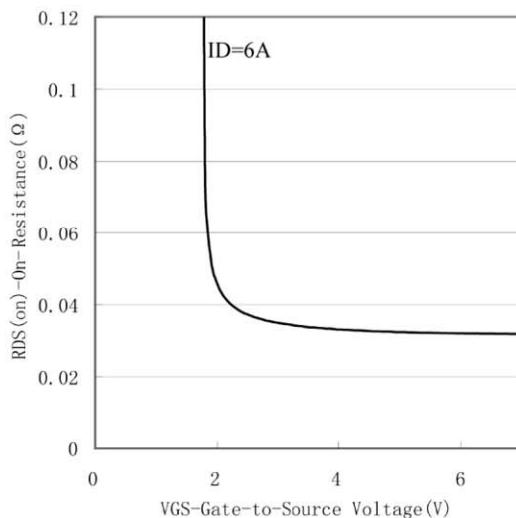
## N-Channel Enhancement Mode MOSFET Typical Characteristics



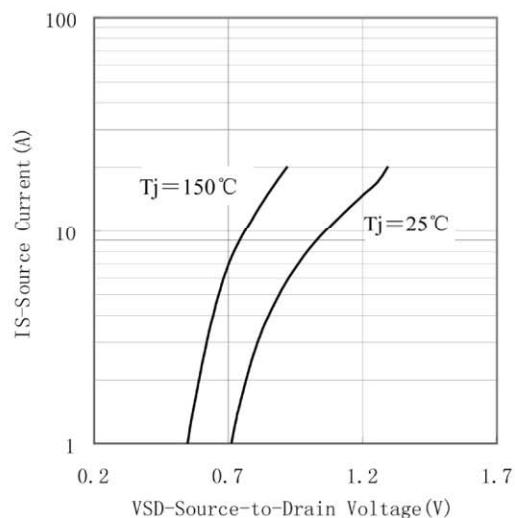
**Figure 5.** On-Resistance Variation with Temperature



**Figure 6.** On-Resistance vs. Drain Current



**Figure 7.** On-Resistance vs. Gate-to-Source Voltage



**Figure 8.** Source-Drain Diode Forward Voltage

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## Package Outline Dimensions (UNIT: mm)

SC-59

